

INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
<i>(use as many sheets as necessary)</i>			
Complete If Known			
Application Number			
Filing Date			
First Named Inventor		Dharmesh Jawarani	
Group Art Unit			
Examiner Name			
Sheet	1	of	2
		Attorney Docket Number	SC13207TP

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
✓4	AA	WO 00/36634	06-22-2000	Bai et al.	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ^	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2
VY	AB	WIELUNSKI, L. et al.; "Alteration of Ni silicide formation by N implantation"; Applied Physics Letters; USA; 01-15-1981; pp 106-108; Vol. 38, No. 2; American Institute of Physics; USA.	
VY	AC	D'HEURLE, F. et al. ; "Diffusion in intermetallic compounds with the CaF ₂ structure: A marker study of the formation of NiSi ₂ thin films"; Journal of Applied Physics; August, 1982; pp 5678-5681; Vol. 53, No. 8; American Institute of Physics; USA.	
VY	AD	CHENG, L.W. et al.; "Effects of nitrogen ion implantation on the formation of nickel silicide contacts on shallow junctions"; Thin Solid Films; 1999; pp 412-416; Elsevier Science S.A..	

Examiner Signature	N. Terrian	Date Considered	01/26/06
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

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NON PATENT LITERATURE DOCUMENTS (cont.)					
✓4	AE	LEE, P.S. et al.; "Improved NiSi Salicide Process using Presilicide N ₂ ⁺ Implant for MOSFETs"; IEEE Electron Device Letters; December, 2000; pp 566-568; IEEE.			
✓	AF	LEE, P.S. et al; "Nickel Silicide Formation on Si(100) and Poly-Si with a Presilicide N ₂ ⁺ Implantation"; Journal of Electronic Materials; 2001; pp 1554-1559; Vol. 30, No. 12; Electronic Materials; USA.			
	AG	CHAO, Tien-Sheng et al.; "Performance Improvement of Nickel Salicided n-Type Metal Oxide Semiconductor Field Effect Transistors by Nitrogen Implantation"; Jpn J. Appl Phys.; April 2002; pp L381-L383; Vol 41; The Japan Society of Applied Physics; Japan.			
	AH	LEE, P.S. et al; "Effect of Ion Implantation on Layer Inversion of Ni Silicided Polu-Si"; Journal of The Electrochemical Society; 2002; ppG505-509; The Electrochemical Society, Inc.			
	AI	CHOI, Chei-Jong et al; "Effects of Hydrogen Implantation on the Structural and Electrical Properties of Nickel Silicide"; Journal of The Electrochemical Society; 2002; pp G517-G521; The Electrochemical Society.			
	AJ	WONG, A.S.W. et al; "F-enhanced morphological and thermal stability of NiSi films onBF ₂ ⁺ -implanted Si(001); Applied Physics Letters; December 30, 2002; pp 5138-5140; Vol 81, No. 27; American Institute of Physics; USA.			
	AK	LAVOIE, C. et al.; "Towards implementation of a nickel silicide process for CMOS technologies"; Article in Press; 2003, pp 1-14; Elsevier B.V.			
	AL	OGHURO, T. et al.; "Nitrogen-doped Nickel Monosilicide Technique for Deep Submicron CMOS Salicide"; IEEE; 1995; pp 18.3.1-18.3.4.			
✓.4	AM	Related application 10/718,892 filed November 21, 2003			
Examiner Signature		<i>V. Yelavar</i>		Date Considered	01/26/06

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